

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	798	opaque near3 oxide	US-PGPUB; USPAT	OR	ON	2009/01/31 14:35
L4	205	3 and (pixel or tft)	US-PGPUB; USPAT	OR	ON	2009/01/31 14:36
L5	136947	yamazaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/31 14:53
L6	5059	5 and @ad<"20010115"	USPAT	OR	ON	2009/01/31 14:54
L7	4610	5 and @ad<"20000115"	USPAT	OR	ON	2009/01/31 14:54
L8	3	6 and (opaque near5 oxide)	USPAT	OR	ON	2009/01/31 14:54
L9	297	6 and data and pixel and tft	USPAT	OR	ON	2009/01/31 14:55
L10	378	6 and data and pixel and semiconductor	USPAT	OR	ON	2009/01/31 15:45
L11	112	6 and data and pixel and semiconductor and passivation	US-PGPUB; USPAT	OR	ON	2009/01/31 15:46
L12	177	6 and pixel and semiconductor and passivation	US-PGPUB; USPAT	OR	ON	2009/01/31 15:46
L13	163	5 and ((gate same below) with (source drain))	US-PGPUB; USPAT	OR	ON	2009/01/31 15:48
L14	9094	(bottom near gate)	US-PGPUB; USPAT	OR	ON	2009/01/31 15:48
L15	4906	(bottom near gate) and (TFT (thin near flim near transistor))	US-PGPUB; USPAT	OR	ON	2009/01/31 15:49
L16	3097	(bottom near gate) and (TFT (thin near flim near transistor)) and (pixel near electrode)	US-PGPUB; USPAT	OR	ON	2009/01/31 15:49
L17	1427	(bottom near gate) and (TFT (thin near flim near transistor)) and (pixel near electrode) and passivation	US-PGPUB; USPAT	OR	ON	2009/01/31 15:49

L18	1427	(bottom near gate) and (TFT (thin near film near transistor)) and (pixel near electrode) and passivation and (oxide insulat\$3 dielectric)	US-PGPUB; USPAT	OR	ON	2009/01/31 15:50
L19	1351	(bottom near gate) and (TFT (thin near film near transistor)) and (pixel near electrode) and passivation and (gate near (oxide insulat\$3 dielectric))	US-PGPUB; USPAT	OR	ON	2009/01/31 15:50
L20	91	19 and @ad<"20000115"	USPAT	OR	ON	2009/01/31 15:50
L21	118	("5151806" "5162901" "5282070" "5285301"). PN. OR ("5459596"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/31 15:53
L22	384	TFT and (anode near (oxidation oxide))	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/31 16:02
L23	117	22 and @ad<"20001115"	USPAT	OR	ON	2009/01/31 16:02
L24	0	"20050173732"	USPAT	OR	ON	2009/01/31 16:10
L25	1	"20050173732"	US-PGPUB; USPAT	OR	ON	2009/01/31 16:10
L26	134	("5247190" "5399502" "5594569" "5643826" "5923962" "5998841" "6046479" "6166397" "6166414" "6172671" "6180982").PN. OR ("6281552").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/31 16:15
L27	10	("5894136" "5962896" "5962916" "5990492" "6046479" "6191452" "6281552").PN. OR ("6509591").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/31 16:34
L32	127	"6281552"	US-PGPUB; USPAT; USOCR	OR	ON	2009/01/31 17:12
L33	354	3 and (pixel or (tft (thin near film)))	US-PGPUB; USPAT	OR	ON	2009/01/31 17:28
L34	10	(3 and (pixel or (tft (thin near film)))) with (improv \$3 increas\$3 decreas\$3 advantage benefi\$4)	US-PGPUB; USPAT	OR	ON	2009/01/31 17:29
L35	2	opaque metal oxide layer	US-PGPUB; USPAT	ADJ	ON	2009/01/31 17:38
L36	17	opaque metal oxide	US-PGPUB; USPAT	ADJ	ON	2009/01/31 17:38

S1	2	"20050173732"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:42
S2	8466	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:44
S3	3086	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	USPAT	OR	ON	2007/04/01 02:44
S4	2156	S3 and oxide and (Cr\$3 Mo\$3 Al\$3)	USPAT	OR	ON	2007/04/01 02:46
S5	1453	S3 and oxide and (Chromium Aluminum Molybdenum)	USPAT	OR	ON	2007/04/01 02:47
S6	862	S5 and @ad<"20020115"	USPAT	OR	ON	2007/04/01 02:47
S7	96	S6 and (low near resistivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:34
S12	6	"5905589"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20
S13	32	"5062689"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20
S14	5387	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/01 23:36
S15	1390	S14 AND TFT and Source and data and gate and insulating and pixel and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:37

S16	1062	S14 AND TFT and Source and data and gate and insulating and pixel and electrode and (Chromium Aluminum Molybdenum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
S17	564	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
S18	255	S17 and @ad<"20020115"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
S19	255	S17 and @ad<"20020115"	US-PGPUB; USPAT	OR	ON	2007/04/01 23:38
S20	286	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
S21	267	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40
S22	193	S14 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride) and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40

S23	137	(opaque with improve) and LCD	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/10/14 13:11
S24	132	(opaque with improve) and LCD	US-PGPUB; USPAT	OR	ON	2007/10/14 13:11
S25	5708	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/10/14 23:00
S28	880	pixel metal oxide opaque block light\$3 tft lcd	US-PGPUB; USPAT	AND	ON	2008/02/17 15:49
S29	314	pixel metal oxide opaque block light\$3 tft lcd	USPAT	AND	ON	2008/02/17 15:50
S30	7071	((438/30) or (257/E21.143) or (257/E21.413) or (438/158)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/02/17 17:54
S31	7484	((438/30) or (257/E21.143) or (257/E21.413) or (438/158)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/09/30 09:13
S32	4048	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	USPAT	OR	ON	2008/09/30 09:13
S33	1843	S32 and oxide and (Chromium Aluminum Molybdenum)	USPAT	OR	ON	2008/09/30 09:13
S34	6313	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)). CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/09/30 09:13
S35	738	S34 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/30 09:13

S36	282	S34 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride) and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/30 09:13
S37	136881	yamazaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/21 09:13
S38	136881	yamazaki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/21 13:19
S39	1	S38 and (opaque near2 oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/21 13:19
S40	406	S38 and (opaque)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/21 13:21
S41	317	S38 and (opaque)	US-PGPUB; USPAT	OR	ON	2009/01/21 13:21
S42	794	opaque near3 oxide	US-PGPUB; USPAT	OR	ON	2009/01/21 14:22
S43	1188	opaque with metal with oxide	US-PGPUB; USPAT	OR	ON	2009/01/21 14:22
S44	4823	opaque same metal same oxide	US-PGPUB; USPAT	OR	ON	2009/01/21 14:22
S45	228	S43 and (TFT (thin near film near transistor))	US-PGPUB; USPAT	OR	ON	2009/01/21 14:23
S46	1	"20050173732"	US-PGPUB; USPAT	OR	ON	2009/01/21 15:18
S47	54	"5985404"	US-PGPUB; USPAT	OR	ON	2009/01/22 08:21
S48	15	"6190963"	US-PGPUB; USPAT	OR	ON	2009/01/22 08:21
S49	1	"20050133841"	US-PGPUB; USPAT	OR	ON	2009/01/22 08:22
S50	1	"7273760"	US-PGPUB; USPAT	OR	ON	2009/01/22 15:21

S51	0	S50 and iro and iridium and protective	US-PGPUB; USPAT	OR	ON	2009/01/22 15:22
S52	0	S50 and iro and iridium and protective	US-PGPUB; USPAT	OR	ON	2009/01/22 15:22
S53	0	S50 and iridium and protective	US-PGPUB; USPAT	OR	ON	2009/01/22 15:22
S54	1	S50 and iridium	US-PGPUB; USPAT	OR	ON	2009/01/22 15:22
S55	1	"20020117700"	US-PGPUB; USPAT	OR	ON	2009/01/22 15:24
S56	20	"1006581"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/22 15:24
S57	14569	(insulat\$3 dielectric) with ((iro ir iro2) (iridium adj oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/22 15:31
S58	586	(insulat\$3 dielectric) near ((iro ir iro2) (iridium adj oxide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/22 15:31
S59	205	(insulat\$3 dielectric) near ((iro ir iro2) (iridium adj oxide))	US-PGPUB; USPAT	OR	ON	2009/01/22 15:31
S60	120	S59 and capacitor	US-PGPUB; USPAT	OR	ON	2009/01/22 15:31
S61	44	S59 and ferroelectric	US-PGPUB; USPAT	OR	ON	2009/01/22 15:32
S62	14	((iridium adj oxide) or (iro2) or (iro)) same protective same ferroelectric	US-PGPUB; USPAT	OR	ON	2009/01/22 16:00
S63	22	((iridium adj oxide) or (iro2) or (iro)) same protective same ferroelectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/22 16:00
S64	579	((iridium adj oxide) or (iro2) or (iro)) same (insulat\$3 dielectric) same ferroelectric	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/01/22 16:01

S65	480	((iridium adj oxide) or (iro2) or (iro)) same (insulat \$3 dielectric) same ferroelectric	US-PGPUB; USPAT	OR	ON	2009/01/22 16:01
S66	237	((iridium adj oxide) or (iro2) or (iro)) same (insulat \$3 dielectric) same ferroelectric	USPAT	OR	ON	2009/01/22 16:01

1/31/2009 7:00:36 PM

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